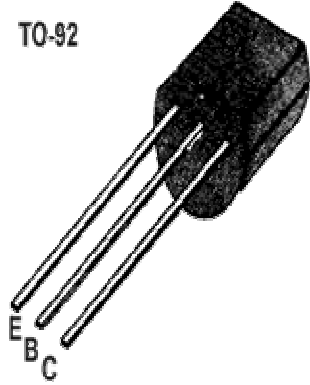


■■ APPLICATION: General purpose switching and amplification.

■■ MAXIMUM RATINGS (Ta=25°C)

PARAMETER	SYMBOL	RATING	UNIT
Collector-base voltage	V _{CBO}	-50	V
Collector-emitter voltage	V _{CEO}	-50	V
Emitter-base voltage	V _{EBO}	-5	V
Collector current	I _C	-150	mA
Collector Power Dissipation	P _C	400	mW
Junction Temperature	T _J	150	°C
Storage Temperature Range	T _{stg}	- 55~150	°C



■■ ELECTRICAL CHARACTERISTICS (Ta=25°C)

PARAMETER	SYMBOL	MIN	TYP.	MAX.	UNIT	TEST CONDITION
DC Current Gain	h _{FE}	70		475		V _{CE} = -5V, I _C = -2mA
Collector Cut-off Current	I _{CBO}			-0.1	μA	V _{CB} = -50V, I _E =0
Emitter Cut-off Current	I _{EBO}			-0.1	μA	V _{EB} = -5V, I _C =0
Collector-Base Breakdown Voltage	BV _{CBO}	-50			V	I _C = -0.1mA, I _E =0
Collector-Emitter Breakdown Voltage	BV _{CEO}	-50			V	I _C = -1mA, I _B =0
Emitter-Base Breakdown Voltage	BV _{EBO}	-5			V	I _E = -0.1mA, I _C =0
Base-emitter Voltage	V _{BE}		-0.69	-0.75	V	V _{CE} = -5V, I _C = -2mA
Collector-Emitter Saturation Voltage	V _{CE(sat)}		-0.25	-0.35	V	I _C = -100mA, I _B = -5mA
Transistion Frequency	f _T		150		MHz	I _C = -1mA, V _{CE} = -10V
Common Base Output Capacitance	C _{ob}		3.5		PF	V _{CB} = -10V, I _E =0, f= 1MHz
Noise Figure	N _F		1.8		dB	V _{CE} = -5V, I _C = -0.2mA, f= 1KHz, R _g = 2K Ω

■■ hFE Classification

Classification	A	B	C	D	E
h _{FE}	70 ~ 105	90 ~ 140	125 ~ 190	176 ~ 260	223 ~ 475